

# IGBT - Field Stop

600 V, 40 A

## FGH40N60SF

### Description

Using novel field stop IGBT technology, ON Semiconductor's field stop IGBTs offer the optimum performance for solar inverter, UPS, welder and PFC applications where low conduction and switching losses are essential.

### Features

- High Current Capability
- Low Saturation Voltage:  $V_{CE(sat)} = 2.3 \text{ V @ } I_C = 40 \text{ A}$
- High Input Impedance
- Fast Switching:  $E_{OFF} = 8 \mu\text{J/A}$
- This Device is Pb-Free and is RoHS Compliant

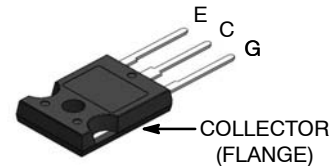
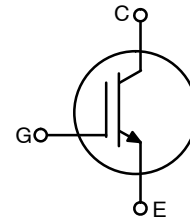
### Applications

- Solar Inverter, UPS, Welder, PFC



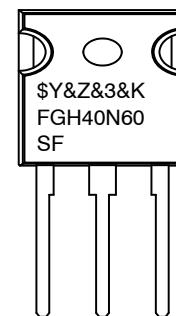
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TO-247-3LD  
CASE 340CK

### MARKING DIAGRAM



\$Y = ON Semiconductor Logo  
&Z = Assembly Plant Code  
&3 = Numeric Date Code  
&K = Lot Code  
FGH40N60SF = Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# FGH40N60SF

## ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Description		Symbol	Ratings	Unit
Collector to Emitter Voltage		$V_{CES}$	600	V
Gate to Emitter Voltage		$V_{GES}$	$\pm 20$	V
Transient Gate-to-Emitter Voltage			$\pm 30$	
Collector Current	$T_C = 25^\circ\text{C}$	$I_C$	80	A
Collector Current	$T_C = 100^\circ\text{C}$		40	A
Pulsed Collector Current	$T_C = 25^\circ\text{C}$	$I_{CM}$ (Note 1)	120	A
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	$P_D$	290	W
Maximum Power Dissipation	$T_C = 100^\circ\text{C}$		116	W
Operating Junction Temperature		$T_J$	-55 to +150	$^\circ\text{C}$
Storage Temperature Range		$T_{stg}$	-55 to +150	$^\circ\text{C}$
Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds		$T_L$	300	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: Pulse width limited by max. junction temperature.

## THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$ (IGBT)	-	0.43	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	-	40	$^\circ\text{C}/\text{W}$

## PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH40N60SFTU	FGH40N60SF	TO-247	Tube	N/A	N/A	30

## ELECTRICAL CHARACTERISTICS OF THE IGBT ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector to Emitter Breakdown Voltage	$BV_{CES}$	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	600	-	-	V
Temperature Coefficient of Breakdown Voltage	$\Delta BV_{CES}/\Delta T_J$	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	-	0.6	-	$\text{V}/^\circ\text{C}$
Collector Cut-Off Current	$I_{CES}$	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	250	$\mu\text{A}$
G-E Leakage Current	$I_{GES}$	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	$\pm 400$	nA

### ON CHARACTERISTICS

G-E Threshold Voltage	$V_{GE(th)}$	$I_C = 250\ \mu\text{A}, V_{CE} = V_{GE}$	4.0	5.0	6.5	V
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	-	2.3	2.9	V
		$I_C = 40\text{ A}, V_{GE} = 15\text{ V}, T_C = 125^\circ\text{C}$	-	2.5	-	V

# FGH40N60SF

## ELECTRICAL CHARACTERISTICS OF THE IGBT ( $T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{ies}$	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	–	2110	–	pF
Output Capacitance	$C_{oes}$		–	200	–	pF
Reverse Transfer Capacitance	$C_{res}$		–	60	–	pF
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 400\text{ V}, I_C = 40\text{ A},$ $R_G = 10\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 25^\circ\text{C}$	–	25	–	ns
Rise Time	$t_r$		–	42	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	115	–	ns
Fall Time	$t_f$		–	27	54	ns
Turn-On Switching Loss	$E_{on}$		–	1.13	–	mJ
Turn-Off Switching Loss	$E_{off}$		–	0.31	–	mJ
Total Switching Loss	$E_{ts}$		–	1.44	–	mJ
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 400\text{ V}, I_C = 40\text{ A},$ $R_G = 10\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 125^\circ\text{C}$	–	24	–	ns
Rise Time	$t_r$		–	43	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	120	–	ns
Fall Time	$t_f$		–	30	–	ns
Turn-On Switching Loss	$E_{on}$		–	1.14	–	mJ
Turn-Off Switching Loss	$E_{off}$		–	0.48	–	mJ
Total Switching Loss	$E_{ts}$		–	1.62	–	mJ
Total Gate Charge	$Q_g$	$V_{CE} = 400\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	–	120	–	nC
Gate to Emitter Charge	$Q_{ge}$		–	14	–	nC
Gate to Collector Charge	$Q_{gc}$		–	58	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CHARACTERISTICS

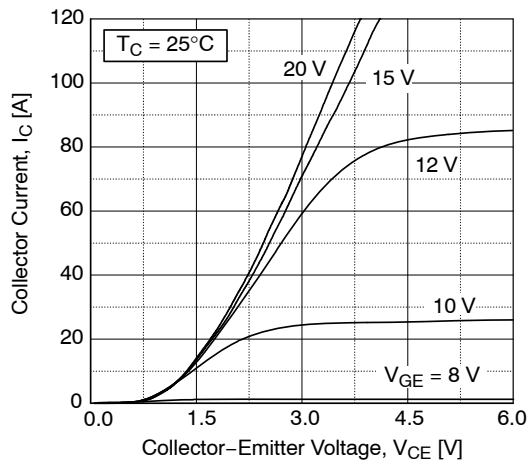


Figure 1. Typical Output Characteristics

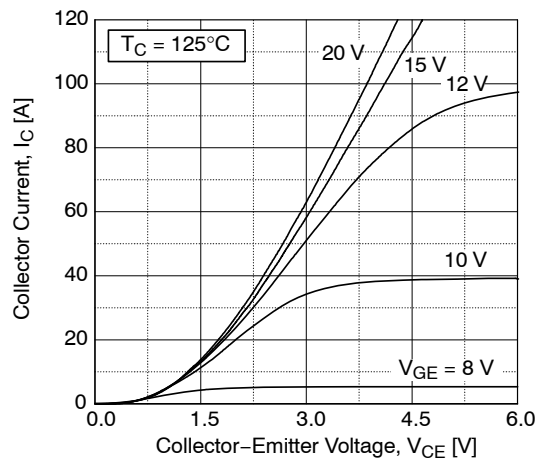


Figure 2. Typical Output Characteristics

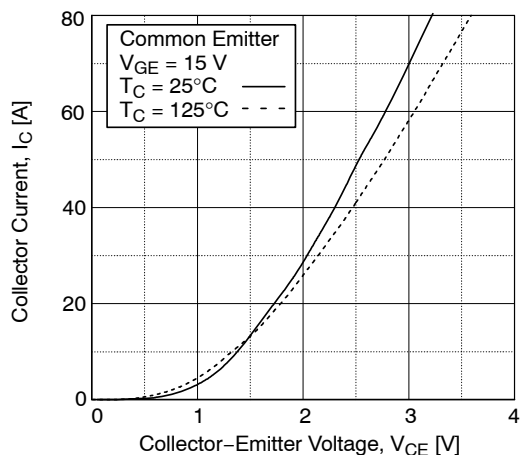


Figure 3. Typical Saturation Voltage Characteristics

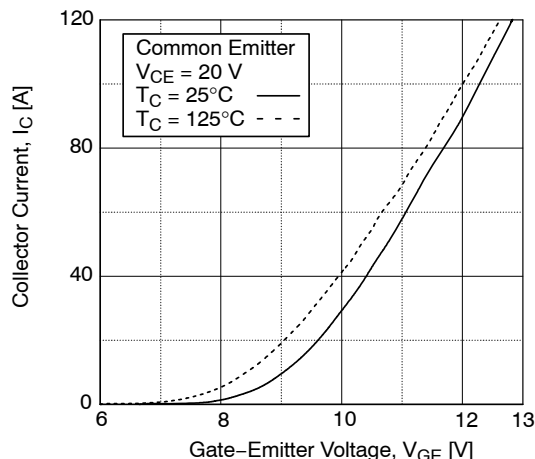


Figure 4. Transfer Characteristics

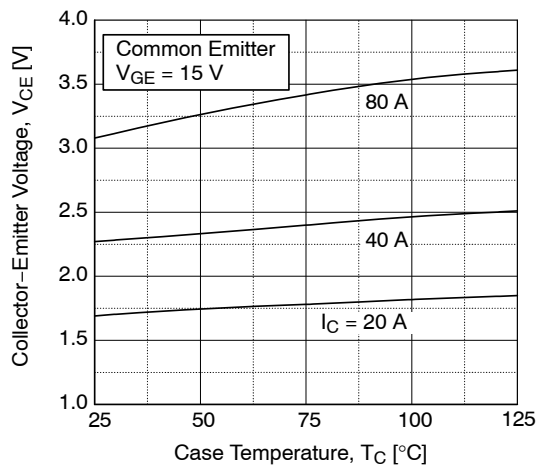


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

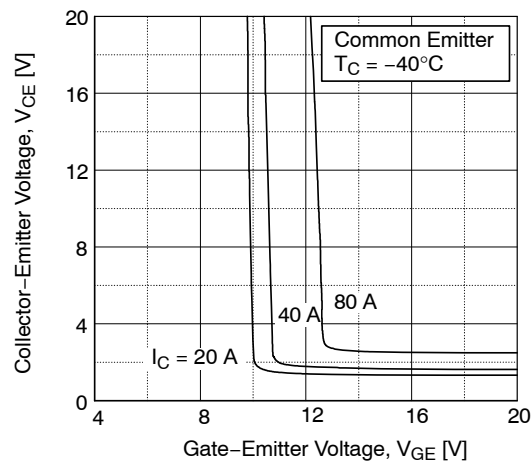


Figure 6. Saturation Voltage vs Vge

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

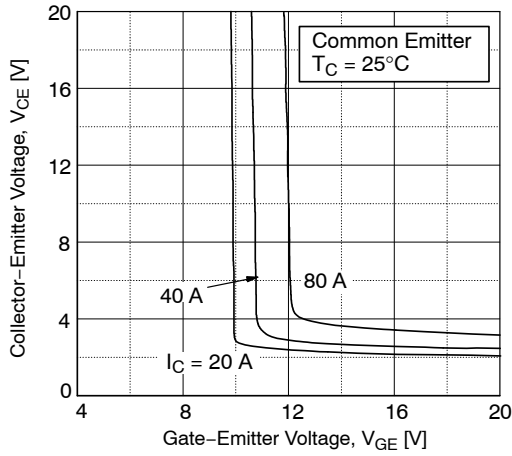


Figure 7. Saturation Voltage vs.  $V_{GE}$

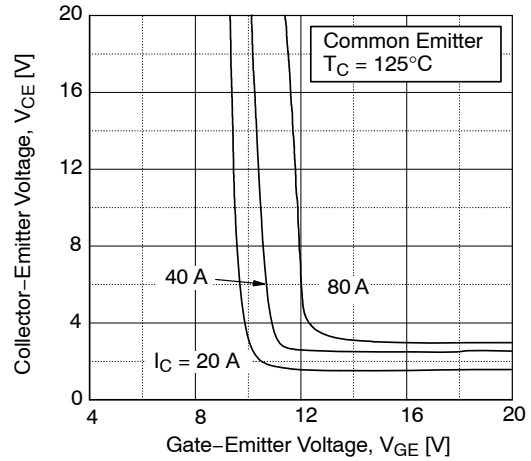


Figure 8. Saturation Voltage vs.  $V_{GE}$

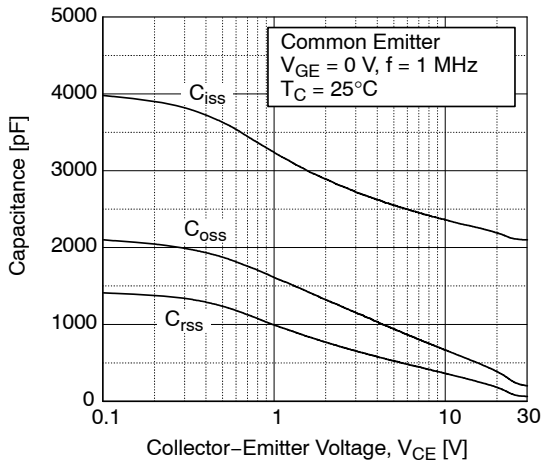


Figure 9. Capacitance Characteristics

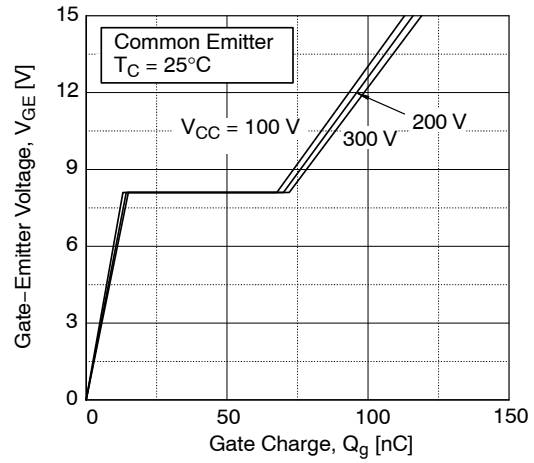


Figure 10. Gate Charge Characteristics

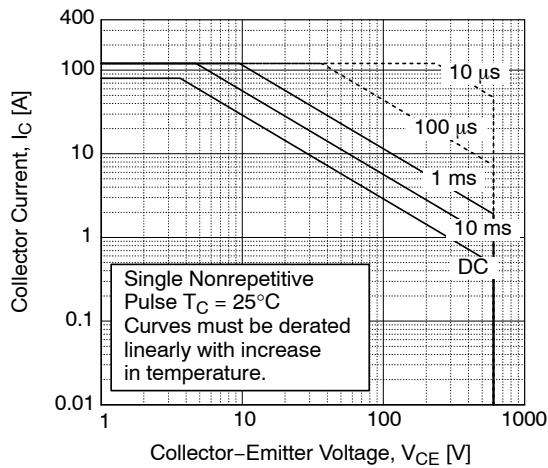


Figure 11. SOA Characteristics

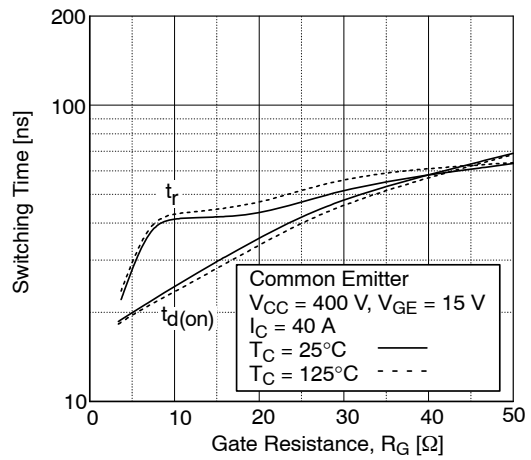


Figure 12. Turn-On Characteristics vs. Gate Resistance

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

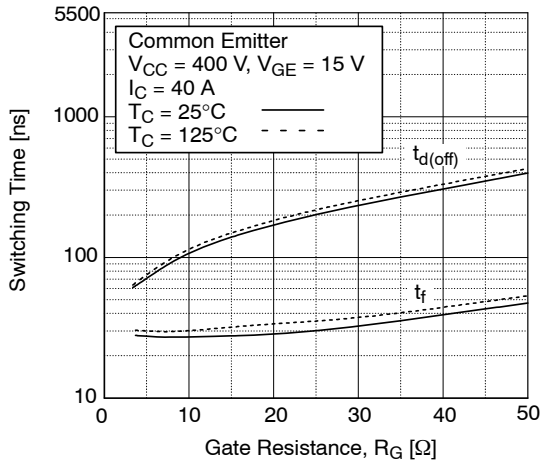


Figure 13. Turn-Off Characteristics vs. Gate Resistance

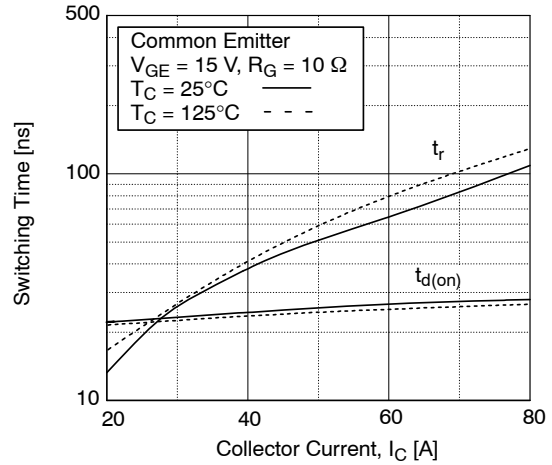


Figure 14. Turn-On Characteristics vs. Collector Current

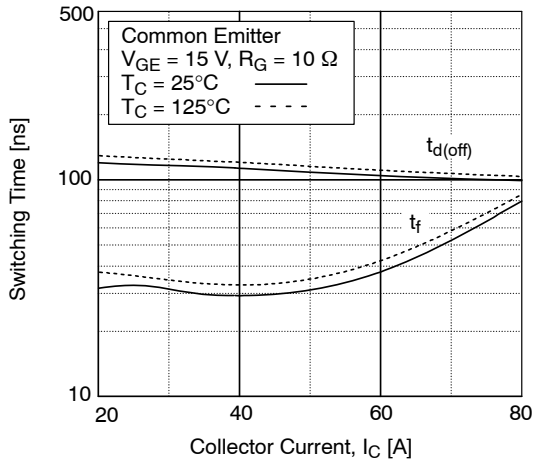


Figure 15. Turn-Off Characteristics vs. Collector Current

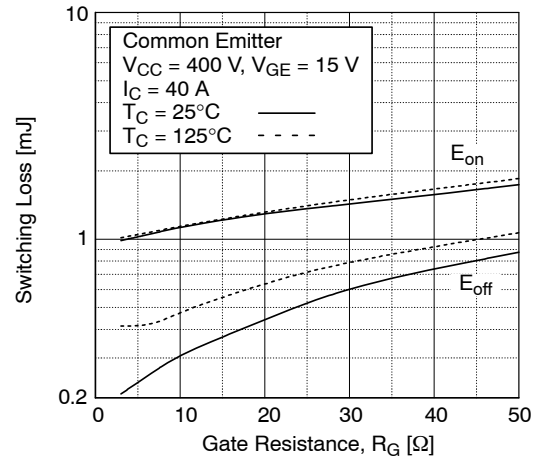


Figure 16. Switching Loss vs. Gate Resistance

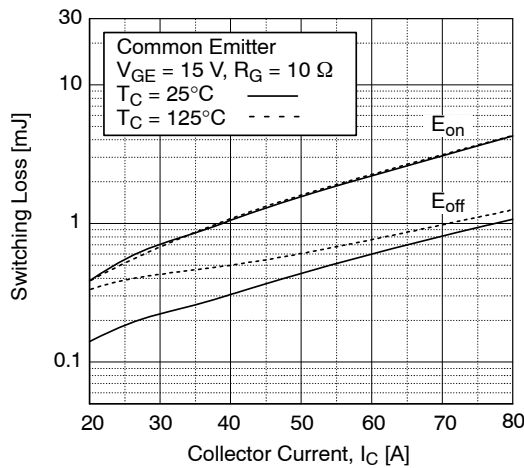


Figure 17. Switching Loss vs. Collector Current

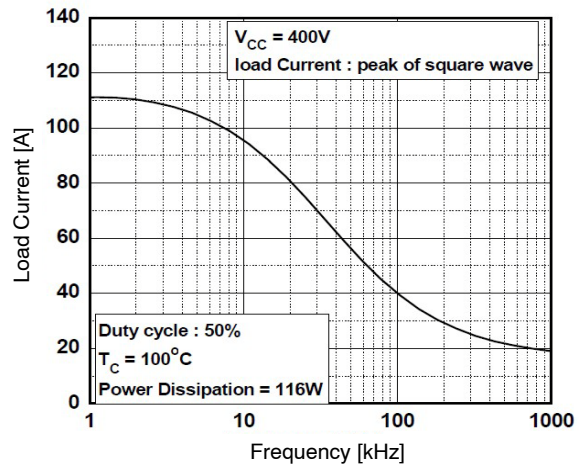


Figure 18. Load Current vs. Frequency

# FGH40N60SF

## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

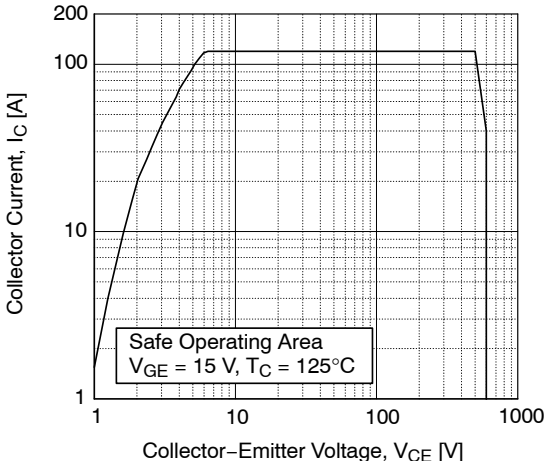


Figure 19. Turn-Off Switching SOA Characteristics

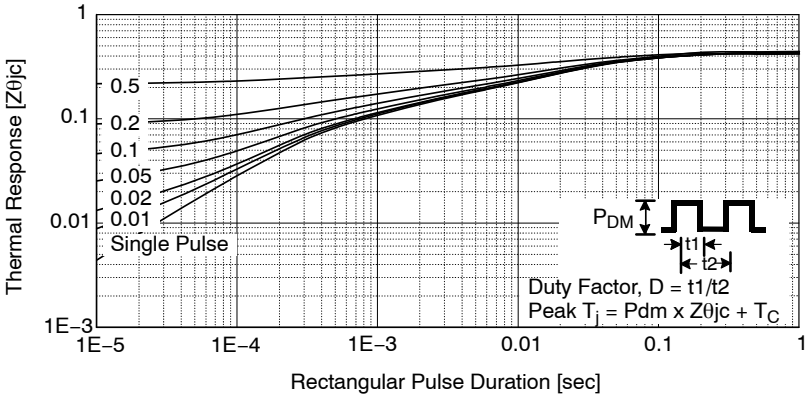
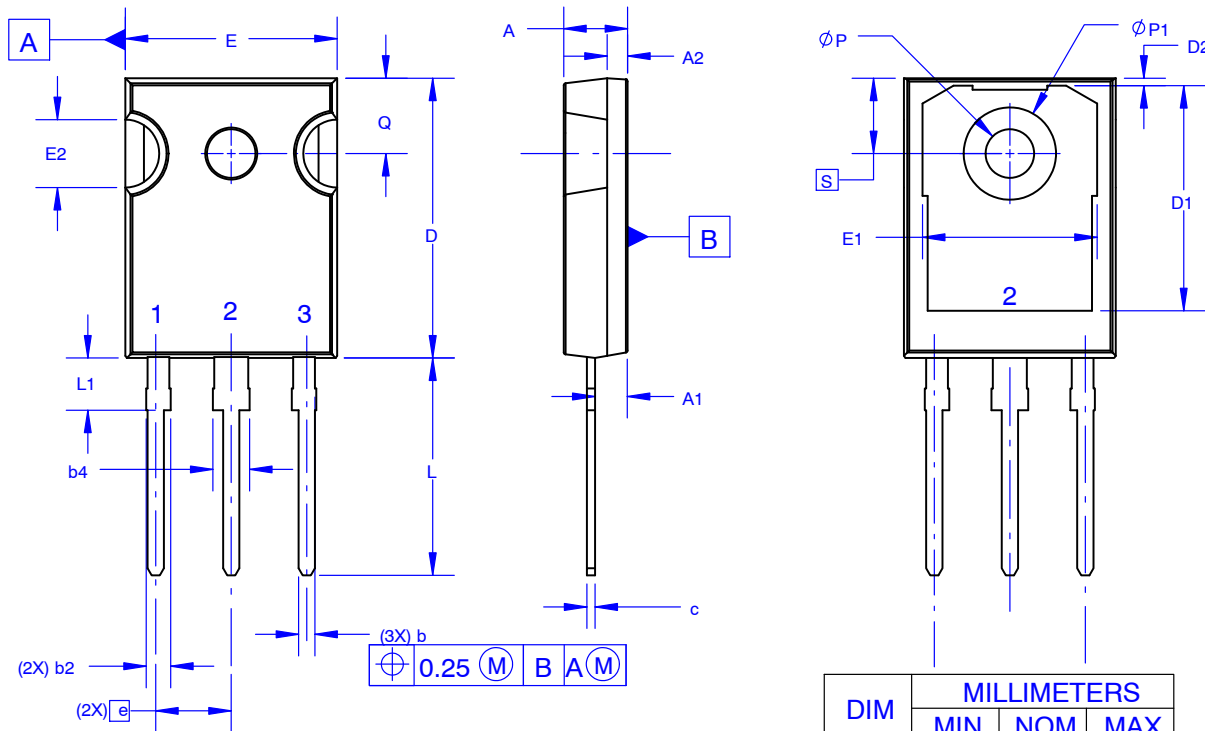


Figure 20. Transient Thermal Impedance of IGBT

TO-247-3LD SHORT LEAD  
CASE 340CK  
ISSUE A

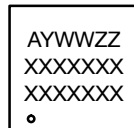
DATE 31 JAN 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC  
MARKING DIAGRAM\*



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Assembly Lot Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	13.08	~	~
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	5.56	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
∅P	3.51	3.58	3.65
∅P1	6.60	6.80	7.00
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

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